

Dual channel digital isolator



SO8-W



SO8-N

Features

- Dual channel, digital isolator with 1 – 1 channel directionality
- High data rate up to 100 Mbps
- Wide Ta range operation: - 40°C to 125°C
- High common-mode transient: >50k V/μs
- From 3 V to 5.5 V supply levels
- 3.3 V and 5 V level translation
- Low power consumption
- Pulse width distortions < 3 ns
- 6k V Galvanic isolation
- SO8 narrow and wide package options

Application

- Optocoupler replacement in industrial application
- Industrial field bus isolation
- Battery monitor and motor drive
- Size-critical multichannel isolation

Description

The **STISO621** are dual-channel digital isolators based on the ST thick oxide galvanic isolation technology.

The devices provide two independent channels in opposite direction with Schmitt trigger input, providing robustness to noise and high speed input/output switching time.

Product status link

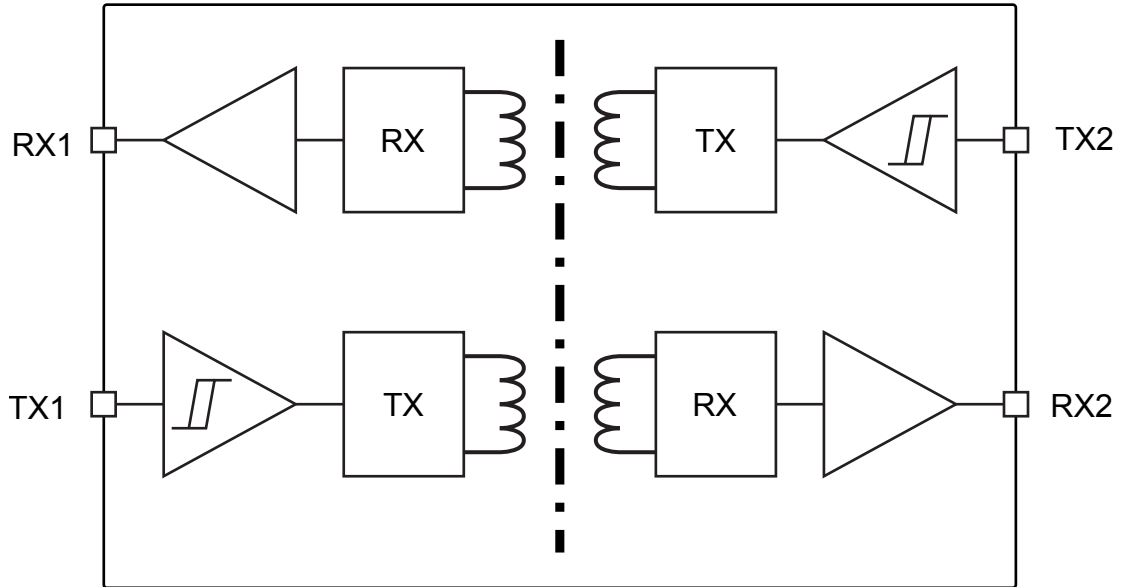
[STISO621](#)

Product label



1 Block diagram

Figure 1. Block diagram



2 Electrical data

2.1 Absolute maximum ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Test Condition	Value	Unit
V_{DDX}	Supply voltage (each side)		-0.3 to 7	V
V_{IN}	Logic input voltage		-0.3 to 7	V
I_O	Output current		5	mA
T_j	Junction temperature		-40 to 150	°C

2.2 Electrical sensitivity

Table 2. ESD protection ratings

Symbol	Parameter	Test Condition	Class	Value	Unit
HBM	Human Body Model	Conforming to ANSI/ESDA/JEDEC JS-001-2014	H2	+/- 2	kV
CDM	Charge Device Model	All pins Conforming to ANSI/ESDA/JEDEC JS-002-2014	C2B	+/- 750	V
MM	Machine Model	Conforming to EIA/JESD22-A115-C	NC	+/- 200	V

2.3 Recommended operating conditions

Table 3. Recommended operating conditions

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
V_{DDX}	Supply voltage (each side)		3		5.5	V
V_{IN}	Logic input voltage		0		5	V
T_{amb}	Ambient temperature		-40		125	°C

2.4 Electrical characteristic

Table 4. Electrical characteristics at $V_{DD1} = V_{DD2} = 5V$

Symbol	Parameter	Test condition	Min.	Typ.	Max.	Unit
V_{DDXon}	V_{DDX} on threshold	V_{DDX} rising from 0 V			2.8	V
$V_{DDXhyst}$	V_{DDX} off hysteresis	V_{DDX} falling from 5 V			0.1	V
IDDX	Supply current	DC		1.65	2	mA
		10 Mbps,		3.65	5	mA

Symbol	Parameter	Test condition	Min.	Typ.	Max.	Unit
IDDX	Supply current	$C_L = 20 \text{ pF}$				
		100 Mbps, $C_L = 20 \text{ pF}$		18	20	mA
V_{IHL}	Low level Schmitt trigger threshold	Logic input falling Full supply range	0.8			V
V_{ILH}	High level Schmitt trigger threshold	Logic input rising Full supply range			2	V
V_{IHyst}	Schmitt trigger input hysteresis				0.5	V
V_{OL}	Low level output voltage	$I_{OH} = 4 \text{ mA}$			0.4	V
V_{OH}	High level output voltage	$I_{OL} = 4 \text{ mA}$	$V_{DDX} - 0.3$			V
Z_O	Output impedance		-40%	50	+40%	Ω
f_{MAX}	Maximum data rate	$V_{IH} = 5 \text{ V}$	100			Mbps
t_r	Output rise time	$C_L = 15 \text{ pF}$		2	4	ns
t_f	Output fall time	$C_L = 15 \text{ pF}$		2	4	ns
t_{DHL}	Propagation delay H to L	See Figure 3		25	42	ns
t_{DLH}	Propagation delay L to H	See Figure 3		25	42	ns
t_{POWUP}	Power-up time				30	μs
$t_{REFRESH}$	Refresh time			1	2	μs
t_{WD}	Watchdog timeout		2		6	μs
PWD	Pulse width distortion $ t_{DHL} - t_{DLH} $	Full temperature range ⁽¹⁾			3	ns
CMTI	Common mode transient immunity	⁽²⁾	50	65		kV/ μs

1. Not tested in production. Limit is guaranteed by characterization on a limited number of samples representing the worst case of production flow.
2. Not tested in production. Limit is guaranteed by characterization on a limited number of samples and simulations.

Note: **Testing conditions: Typical values are defined at $T_{amb} = 25^\circ\text{C}$ and $V_{DD1} = V_{DD2} = 5 \text{ V}$, minimum and maximum limits applies to the full temperature range (Tested in production at $T_{amb} = 25^\circ\text{C}$ and the limits in the full temperature range are guaranteed by characterization on a limited quantity of samples), unless otherwise specified.**

Table 5. Electrical characteristics at $V_{DD1} = V_{DD2} = 3\text{V}$

Symbol	Parameter	Test condition	Min.	Typ.	Max.	Unit
V_{DDXon}	V_{DDX} on threshold	V_{DDX} rising from 0 V			2.8	V
$V_{DDXhyst}$	V_{DDX} off hysteresis	V_{DDX} falling from 5 V			0.1	V
I_{DDX}	Supply current	DC		1.5	2	mA
		10 Mbps, $C_L = 20 \text{ pF}$		3	5	mA
		100 Mbps, $C_L = 20 \text{ pF}$		11	20	mA

Symbol	Parameter	Test condition	Min.	Typ.	Max.	Unit
V _{IHL}	Low level Schmitt trigger threshold	Logic input falling Full supply range	0.8			V
V _{ILH}	High level Schmitt trigger threshold	Logic input rising Full supply range			2	V
V _{IHyst}	Schmitt trigger input hysteresis				0.5	V
V _{OL}	Low level output voltage	I _{OH} = 4 mA			0.4	V
V _{OH}	High level output voltage	I _{OL} = 4 mA	V _{DDX} – 0.3			V
Z _O	Output impedance		-40%	50	+40%	Ω
f _{MAX}	Maximum data rate	V _{IH} = 3.3 V	100			Mbps
t _r	Output rise time	C _L = 15 pF		1.5	4	ns
t _f	Output fall time	C _L = 15 pF		1.5	4	ns
t _{DHL}	Propagation delay H to L	See Figure 3		25	42	ns
t _{DLH}	Propagation delay L to H	See Figure 3		25	42	ns
t _{POWUP}	Power-up time				30	μs
t _{REFRESH}	Refresh time			1	2	μs
t _{WD}	Watchdog timeout		2		6	μs
PWD	Pulse width distortion t _{DHL} – t _{DLH}	Full temperature range ⁽¹⁾			3	ns
CMTI	Common mode transient immunity	⁽²⁾	50	65		kV/μs

1. Not tested in production. Limit is guaranteed by characterization on a limited number of samples representing the worst case of production flow.

2. Not tested in production. Limit is guaranteed by characterization on a limited number of samples and simulations.

Note: **Testing conditions: Typical values are defined at T_{amb} = 25°C and VDD1 = VDD2 = 3 V, minimum and maximum limits applies to the full temperature range (Tested in production at T_{amb} = 25°C and the limits in the full temperature range are guaranteed by characterization on a limited quantity of samples), unless otherwise specified.**

3 Isolation characteristics

Table 6. Isolation specifications

Parameter	Symbol	Conditions	Value		Unit
			SO8-W	SO8-N	
Clearance(Minimum external air gap)	CLR	Measured from input terminals to output terminals, shortest distance through air	8	4	mm
Creepage(Minimum external tracking)	CPG	Measured from input terminals to output terminals, shortest distance path along body	8	4	mm
Comparative Tracking Index (Tracking resistance)	CTI	DIN IEC 112/VDE 0303 Part 1	≥ 400	≥ 400	V
Isolation Group		Material Group (DIN VDE 0110, 1/89, Table 1)	II	II	

Table 7. Isolation characteristics

Parameter	Symbol	Test Conditions	Characteristic		Unit
			SO8-W	SO8-N	
Maximum repetitive isolation voltage	V_{IORM}	AC voltage (bipolar)	1200	1200	V_{PEAK}
Maximum working isolation voltage	V_{IOWM}	AC voltage (sine wave); time-dependent dielectric breakdown (TDDb) test	849	849	V_{RMS}
Input to output test voltage ⁽¹⁾	V_{PR}	Method a, type test $V_{PR} = V_{IORM} \times 1.6$, $t_m = 10$ s Partial discharge < 5 pC	1920	1920	V_{PEAK}
		Method b, 100 % production test $V_{PR} = V_{IORM} \times 1.875$, $t_m = 1$ s Partial discharge < 5 pC	2250	2250	V_{PEAK}
Isolation withstand voltage ⁽²⁾	V_{ISO}	1min (type test)	3536 / 5000	2828 / 4000	V_{RMS} V_{PEAK}
Isolation test voltage ⁽²⁾	$V_{ISOtest}$	1sec (100% production)	6000	4800	V_{PEAK}
Transient overvoltage (Highest allowable overvoltage)	V_{IOTM}	$t_{ini} = 60$ s Type test	6000	4800	V_{PEAK}
Maximum surge isolation Voltage	V_{IOSM}	Type test	6000	4800	V_{PEAK}
Isolation resistance	R_{IO}	$V_{IO} = 500$ V at T_S Type test	$>10^9$	$>10^9$	Ω

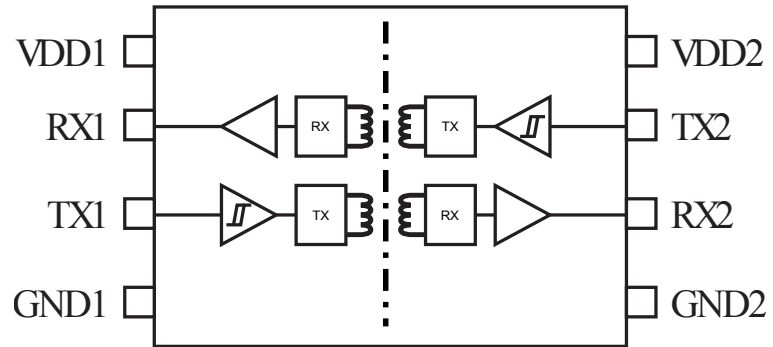
1. Test performed in accordance with VDE 0884-10.

2. Test performed in accordance with UL 1577.

Note: For three-phase systems the values in the table refer to the line-to-neutral voltage.

4 Pin connection

Figure 2. Pin connection (top view)



5 Pin list

Table 8. Pin description

N.	Name	Type	Function
1	VDD1	Supply	Supply voltage side 1
2	RX1	Logic output	Receive data side 1
3	TX1	Logic input	Transmit data side 1
4	GND1	Ground	Ground side 1
5	GND2	Ground	Ground side 2
6	RX2	Logic output	Receive data side 2
7	TX2	Logic input	Transmit data side 2
8	VDD2	Supply	Supply voltage side 2

6 Description

The STISO621 is a dual high-speed isolated communication channel. It integrates one channel for each communication direction and provides low levels of pulse width distortion in the full operation range.

6.1 Device operation

The device operation is described in the following table:

Table 9. Device operation table

VDD1	VDD2	TX1	RX2	TX2	RX1
Above UVLO	Above UVLO	H	H	H	H
		L	L	H	H
		H	H	L	L
		L	L	L	L
Below UVLO	Above UVLO	X	L ⁽¹⁾	X	Unknown
Above UVLO	Below UVLO	X	Unknown	X	L ⁽¹⁾
Below UVLO	Below UVLO	X	Unknown	X	Unknown

1. Safe state imposed by default after the watchdog timeout.

Figure 3. Timing diagram

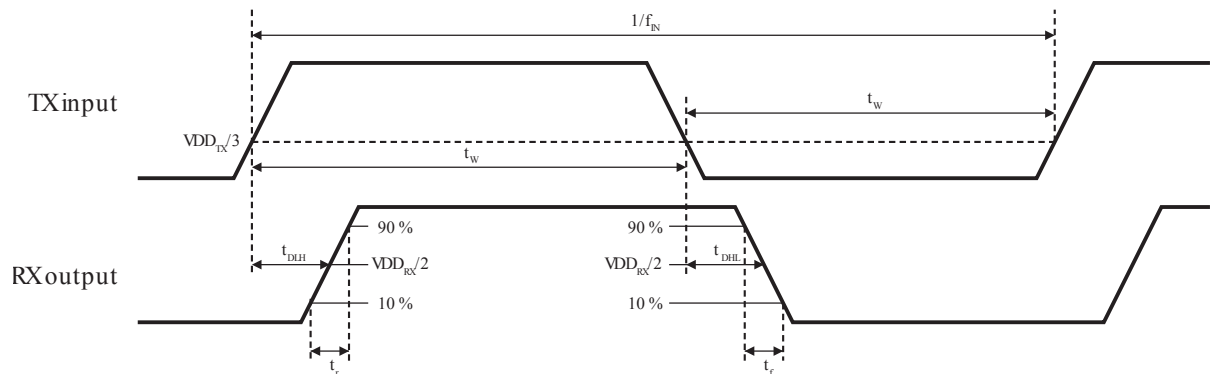
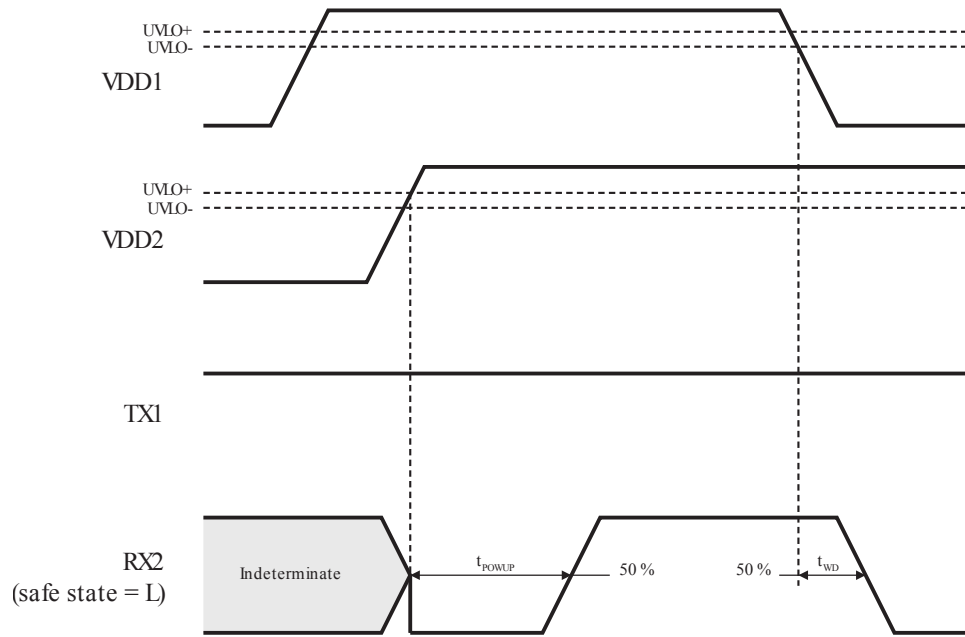


Figure 4. Timing diagram – power up and power down



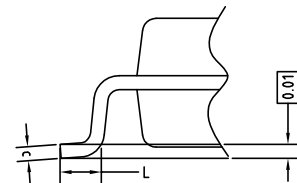
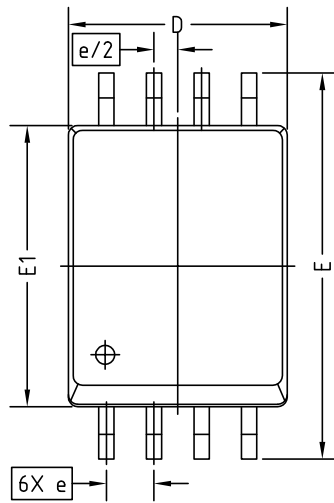
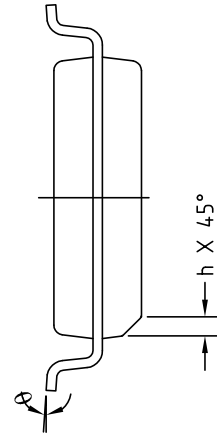
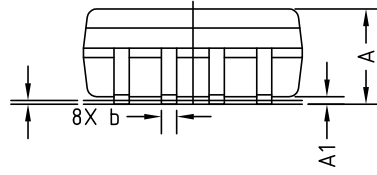
7 Package mechanical data

Table 10. SO8 wide package dimensions

Symbol	Min.	Nom.	Max.	Note
A	2.34		2.64	
A1	0.10		0.30	
b	0.30		0.51	
c	0.20		0.33	
D	5.64		6.05	
e	1.27 BSC			
E1	7.39		7.59	
E	10.11		10.52	
L	0.61		0.91	
h	0.25		0.76	
θ	0°		8°	
aaa		0.25		
bbb		0.25		
ccc		0.10		

Figure 5. SO8 wide package drawings

SIDE VIEW



TOP VIEW

Figure 6. SO8 wide package recommended footprint

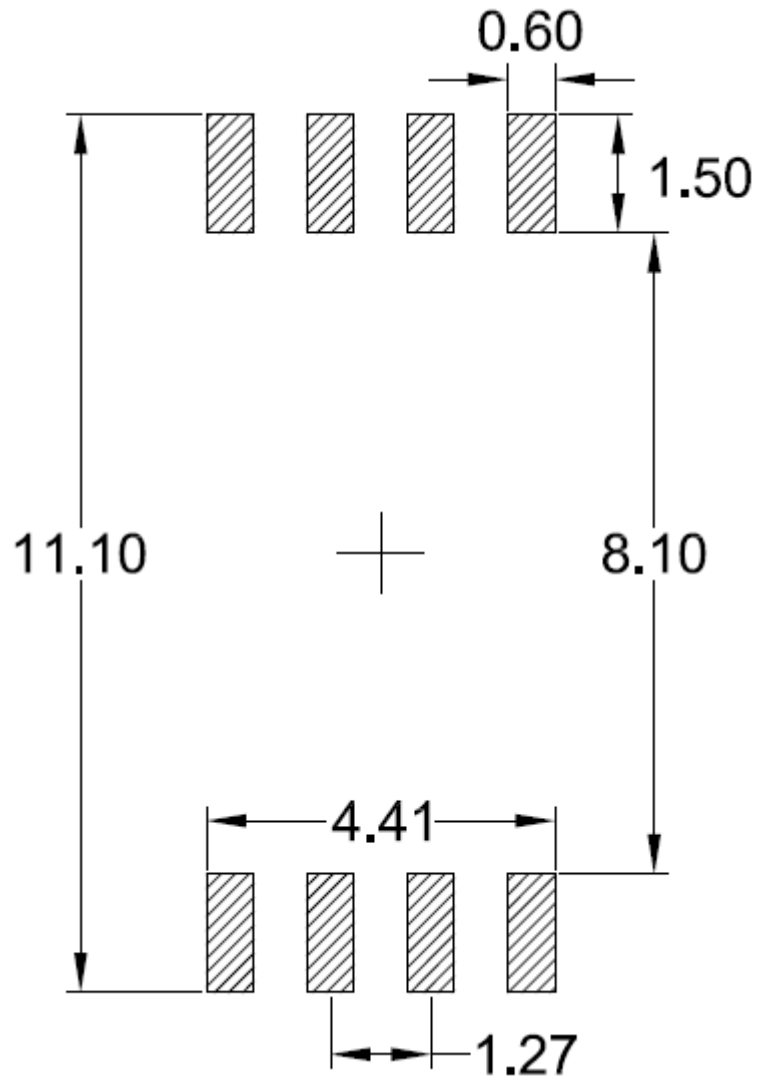


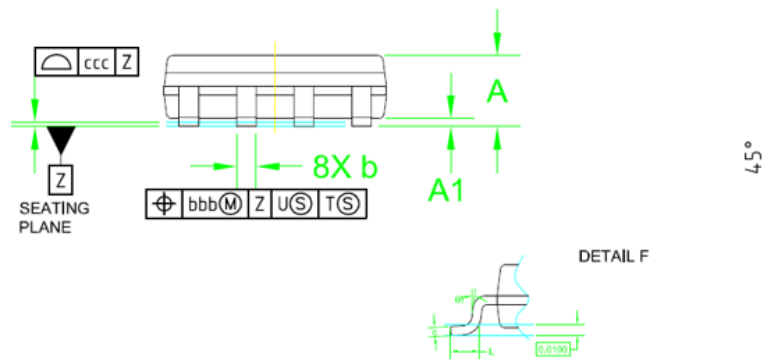
Table 11. SO8 narrow package dimensions

Symbol	Min.	Nom.	Max.
A	1.35		1.75
A1	0.10		0.25
b	0.35		0.49
c	0.19		0.25
D	4.80		5.00
e	1.27BSC		
E1	3.80		4.00
E	5.80		6.20
L	0.40		1.25
h	0.25		0.50
θ	0°		7°

Symbol	Min.	Nom.	Max.
$\Theta 1$	2°		12*
aaa		0.25	
bbb		0.25	
ccc		0.10	

Figure 7. SO8 narrow package drawings

SIDE VIEW



TOP VIEW

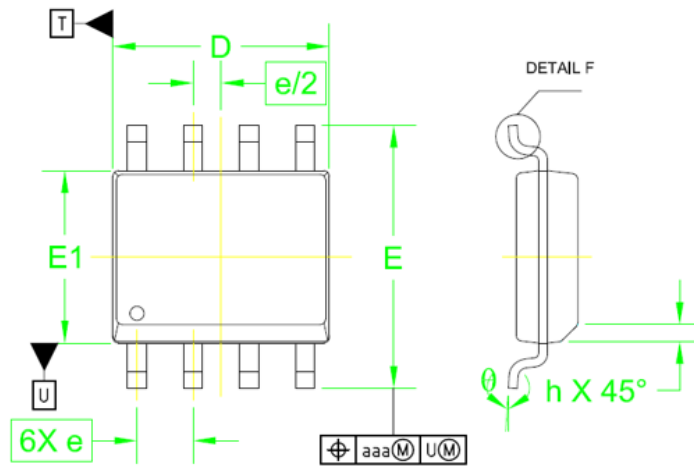
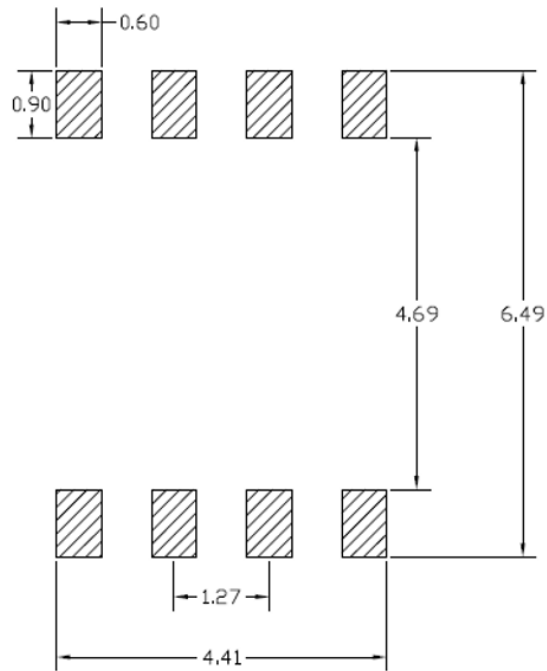


Figure 8. SO8 narrow package recommended footprint



8 Order Information

Table 12. Order Information

Order Code	Package	Packing
STISO621W	S08 wide body	Tube
STISO621WTR	S08 wide body	Tape & Reel
STISO621	S08 narrow body	Tube
STISO621TR	S08 narrow body	Tape & Reel

Revision history

Table 13. Document revision history

Date	Version	Changes
03-Aug-2020	1	Initial release.
23-Mar-2020	2	SO8 narrow body package option added.
09-May-2022	3	Updated Section 1 Block diagram and Section 4 Pin connection

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